

TO-92 Plastic-Encapsulate Transistors

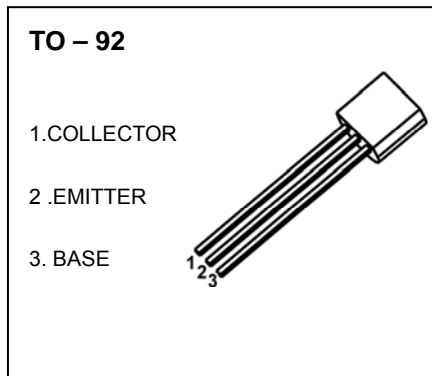
BF240 TRANSISTOR (NPN)

FEATURES

- General Purpose Switching and Amplification.

MAXIMUM RATINGS (T_a=25°C unless otherwise noted)

Symbol	Parameter	Value	Unit
V _{CBO}	Collector-Base Voltage	40	V
V _{CEO}	Collector-Emitter Voltage	40	V
V _{EBO}	Emitter-Base Voltage	4	V
I _C	Collector Current	25	mA
P _C	Collector Power Dissipation	300	mW
R _{θJA}	Thermal Resistance From Junction To Ambient	416	°C/W
T _j	Junction Temperature	150	°C
T _{stg}	Storage Temperature	-55~+150	°C



ELECTRICAL CHARACTERISTICS (T_a=25°C unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	V _{(BR)CBO}	I _C = 0.1mA, I _E =0	40			V
Collector-emitter breakdown voltage	V _{(BR)CEO}	I _C =1mA, I _B =0	40			V
Emitter-base breakdown voltage	V _{(BR)EBO}	I _E =100μA, I _C =0	4			V
Collector cut-off current	I _{CBO}	V _{CB} =20V, I _E =0			0.1	μA
Emitter cut-off current	I _{EBO}	V _{EB} =4V, I _C =0			0.1	μA
DC current gain	h _{FE}	V _{CE} =10V, I _C =1mA	67		220	
Collector-emitter saturation voltage	V _{CE(sat)}	I _C =10mA, I _B =1mA			0.3	V
Base-emitter voltage	V _{BE}	V _{CE} =10V, I _C =1mA			0.775	V
Transition frequency	f _T	V _{CE} =10V, I _C = 1mA, f=100 MHz	150			MHz